ISFAHAN





Never Stand Still

Faculty of Engineering

School of Photovoltaic and Renewable Energy Engineering

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Outline



- Introduction to organic-inorganic metal halide perovskite semiconductors used in optoelectronic devices,
- Development of luminescence imaging technique for perovskite solar cells :
 - ✓ Investigation of the light stability of perovskite solar cells,
- Investigate the excitonic characteristics of perovskites:
 - ✓ Excitonic binding energy (Ry^*) and reduced mass (m^*)
 - ✓ Impact of:
 - Microstructure,
 - Polarons,



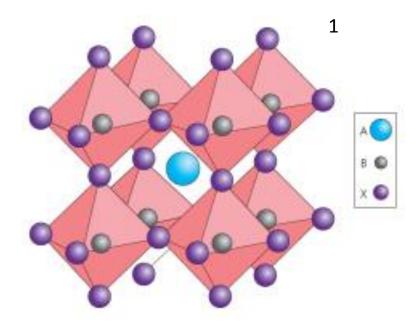


Organic-inorganic metal halide perovskite semiconductors:

• General formula ABX₃:

 $A = CH_3NH_3^+, H_2N-CH=NH_2^+, Cs^+, Rb^+; B = Pb^{2+}, Sn^{2+}; X = I^-, Br^-;$

- Applications:
 - ✓ Photo-detectors,
 - ✓ Light-emitting diodes,
 - ✓ Photovoltaics,





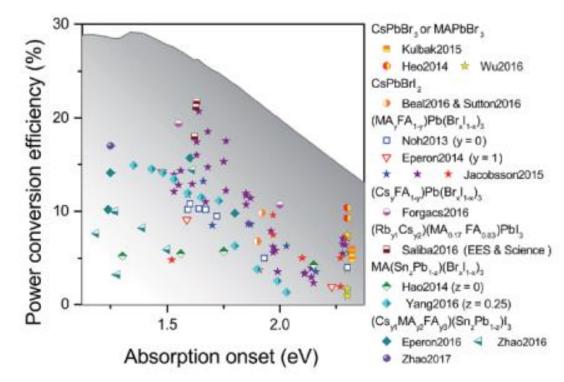


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 - ✓ Photo-detectors,
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 - Pros:
 - Bandgap tunability²,



²Eva Unger et al, Material Chemistry A (2017)

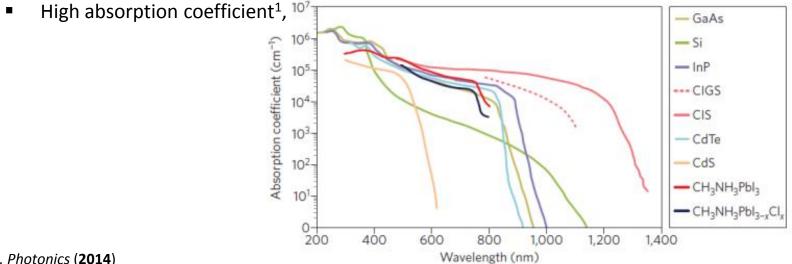


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¹Martin Green *et al, Nat. Photonics* (2014)

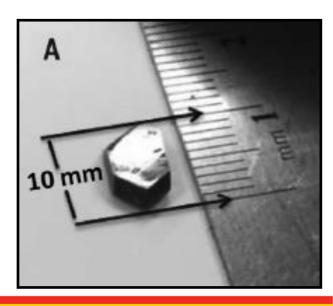


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 - High absorption coefficient¹,
 - Long charge-carrier diffusion length
 (> 175 μm in single crystal)³





³Qingfeng Dong et al, Science (2015)



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 - Low exciton binding energy,





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- Applications:
 - ✓ Photo-detectors,
 - ✓ Light-emitting diodes,
 - ✓ Photovoltaics,
 - o Cons:
 - Charge-carrier non-radiative recombination losses⁴,

Polycrystalline perovskite ~ 10¹⁵-10¹⁷ cm⁻³

CIGS ~ 10¹³ cm⁻³

Single crystal perovskite ~ 10⁹-10¹² cm⁻³





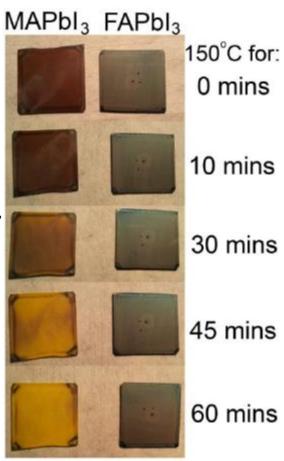


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 - Charge-carrier non-radiative recombination losses,
 - Long-term stability (light, temperature and moisture)⁵,





⁵Eperon *et al, Energy* & *Environ. Sci.* (2014)

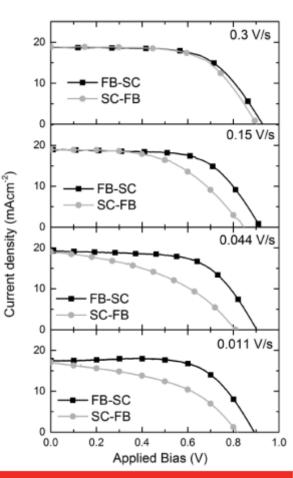


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 - ✓ Photo-detectors,
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 - ✓ Photovoltaics,
 - **Cons:**
 - Charge-carrier non-radiative recombination losses,
 - Long-term stability (light, temperature and moisture)
 - Photo-current hysteresis in *J-V* (voltage range, sweep rate and sweep direction)⁶,





⁶Snaith et al, J. Phys. Chem. Letters (2014)

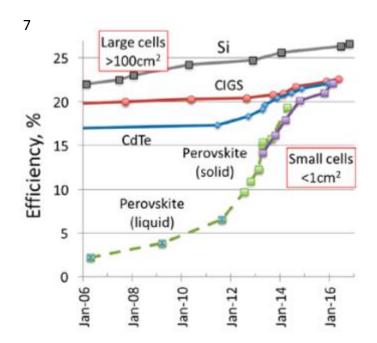


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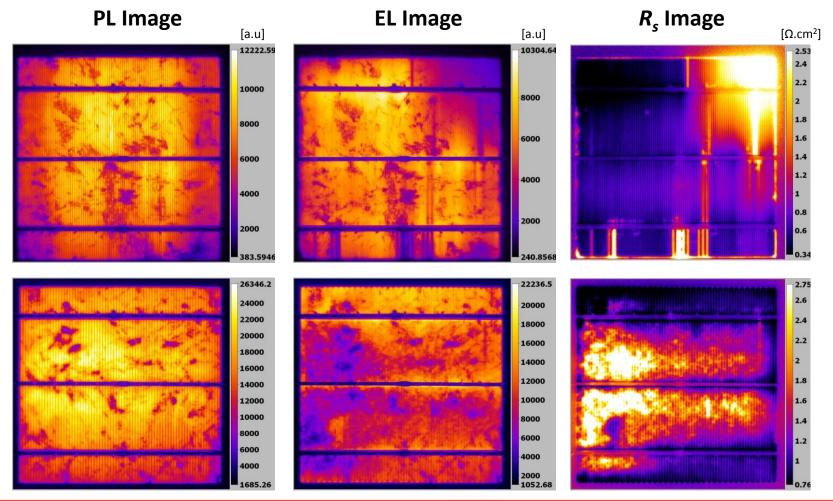
⁷Green & Ho-Baillie, ACS Energy Letters (2017)



Luminescence Imaging Studies



• Photoluminescence (PL) and electroluminescence (EL) imaging have been widely and successfully being used in the silicon PV community.

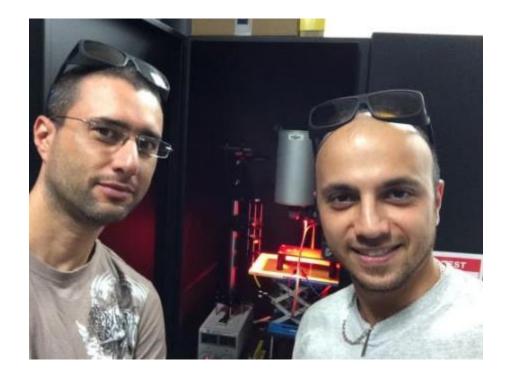




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Luminescence Imaging Studies



- Photoluminescence (PL) and electroluminescence (EL) imaging has been widely and successfully being used in the silicon PV community.
- Luminescence imaging speeds up reliable characterization and inspection of solar cell.
- For the first time, the validity of the Planck's generalized emission law was investigated for perovskite solar cells through PL and EL imaging.⁸
- The impact of pre-treatment of the device such as *light-soaking* was examined on the Planck's law.⁸
- Degradation in dark investigated and J-V performance was assessed using imaging.⁹
- Luminescence imaging is also used to investigate the:¹⁰
 - Immediate device response to light current-voltage and light-soaking measurements.
 - Long-term device response to light current-voltage and light-soaking measurements.

⁸Ziv Hameiri, Arman Mahboubi Soufiani et al, PIP 23,1697 (2015)
 ⁹Arman Mahboubi Soufiani et al, JAP 120, 035702 (2016)
 ¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. 7, 1602111 (2016)

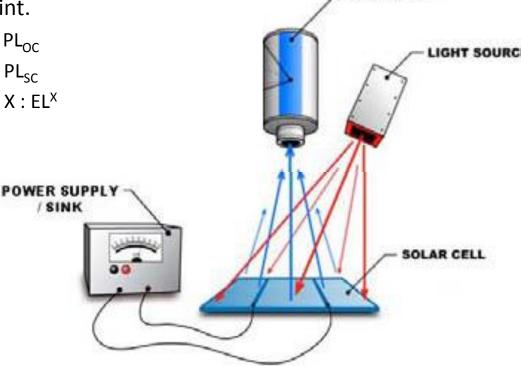


Luminescence Imaging Measurement Setup

- Excitation source: 635 nm light emitting diode (LED).
- Detection system: Silicon charge-coupled device (CCD) camera with 100 milliseconds resolution.
- LED tail spectrum is filtered out using SP filters.
- Reflection from the device is filtered out

using LP filters at the detection point.

- ✓ PL at open-circuit condition : PL_{oc}
- ✓ PL at short-circuit condition : PL_{SC}
- ✓ EL at terminal voltage bias of $X : EL^X$

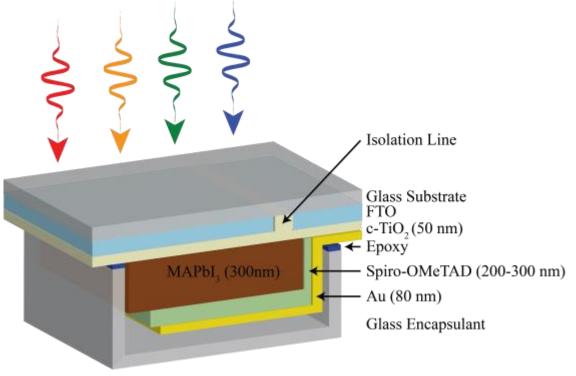


PL CAME



Device Structure

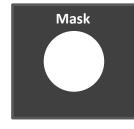
- Planar *CH*₃*NH*₃*PbI*₃ based solar cells fabricated via *gas-assisted* technique.¹⁰
- *c-TiO*₂ as the electron selective and *Spiro-OMeTAD* as the hole selective contacts.
- Device active area ≈ 8 x 8 mm²
- Aperture Diameter = 4.5 mm

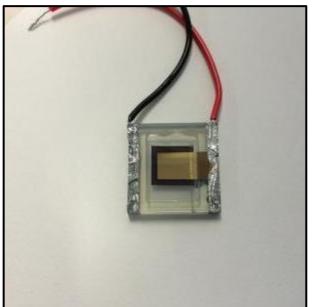


¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. **7**, 1602111 (2016)



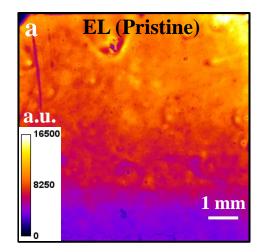


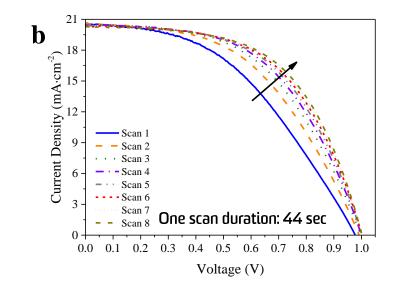




Effect of Prolonged Illumination





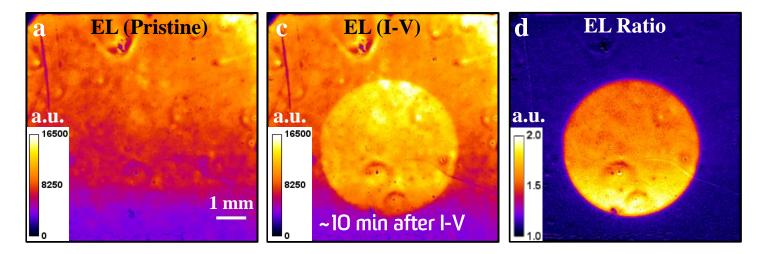


¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. **7**, 1602111 (2016)



Initial Observations after I-V Measurements: EL and PLoc





$$\phi_{em}(E) \propto EQE_{PV}(E) \exp\left(\frac{V_j}{V_{th}}\right)$$

- ϕ_{em} : EL intensity
- EQE_{PV} : Photovoltaic external quantum efficiency
 - V_{i} : Junction voltage

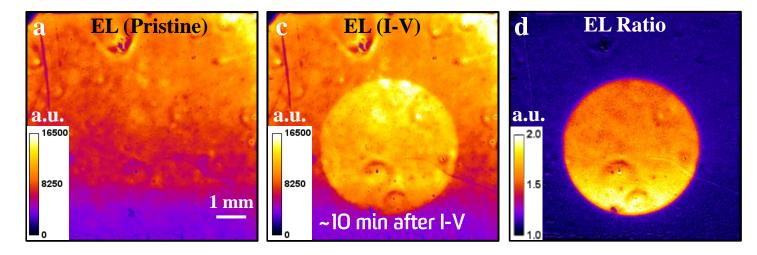
¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. 7, 1602111 (2016)

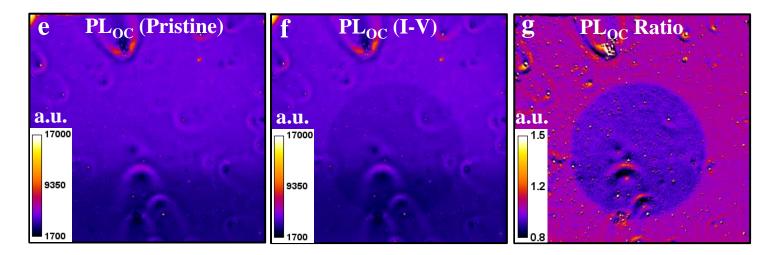
- E: Energy
- V_{th} : Thermal voltage



Initial Observations after I-V Measurements: EL and PLoc



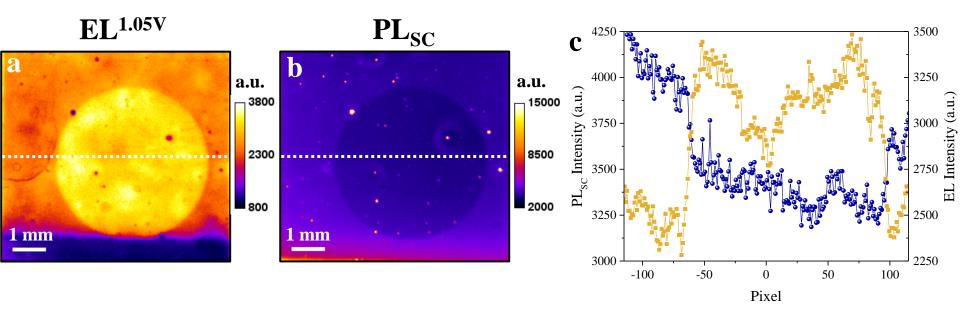




¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. 7, 1602111 (2016)







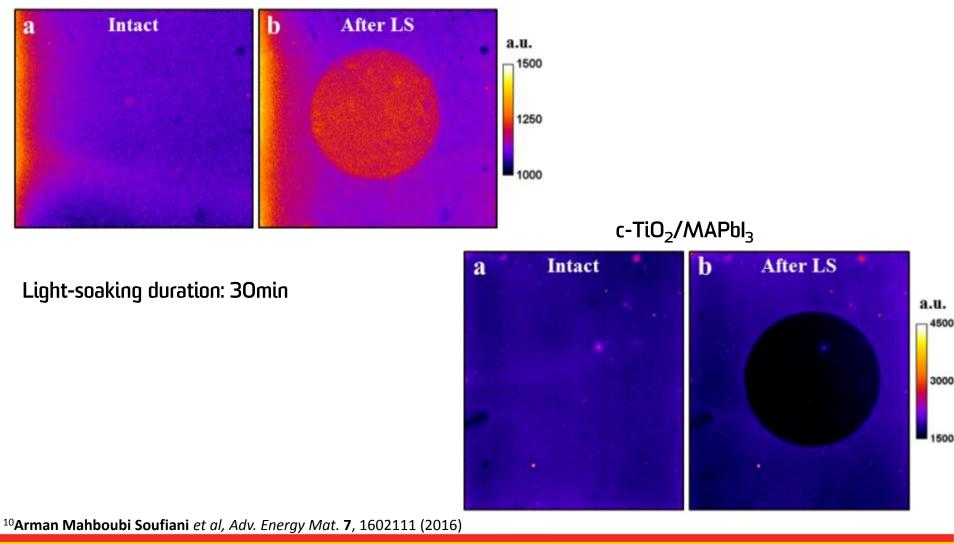
¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. **7**, 1602111 (2016)



Light-soaked Bilayers: PL_{oc}



MAPbl₃/Spiro-OMeTAD







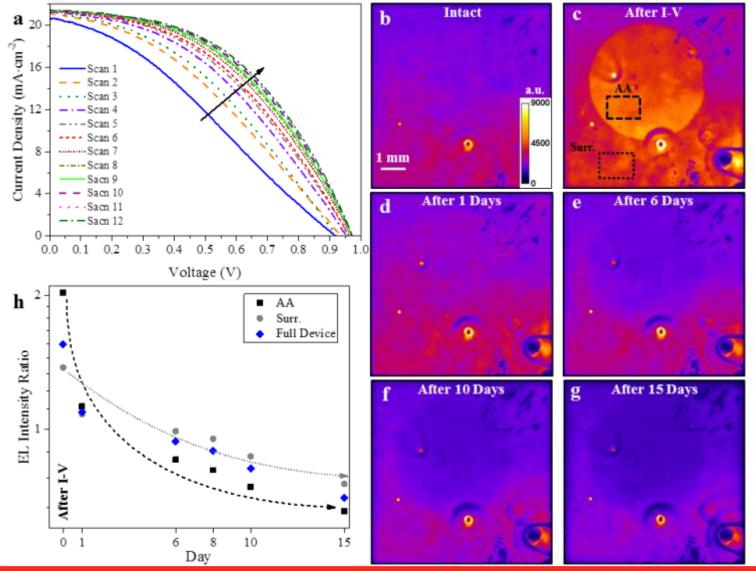
- Series resistance (interfacial): Improved.
- Bulk non-radiative recombination: **Possibly Reduced.**
- Front surface non-radiative recombination: Increased.
- Back surface non-radiative recombination: **Possibly Increased?**

¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. 7, 1602111 (2016)



Long-term Evolution of EL

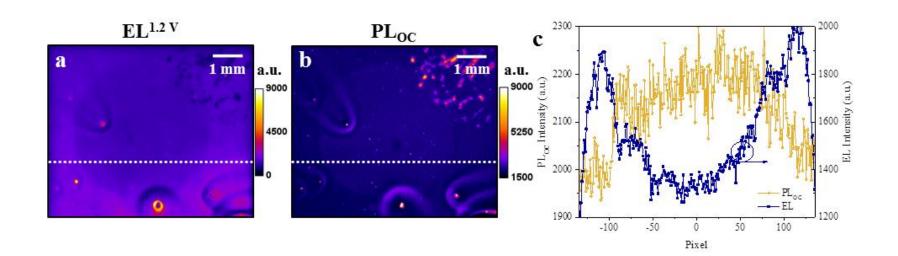






Long-term Evolution of PL_{oc}



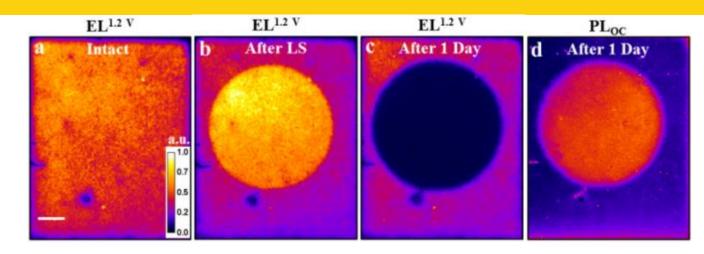


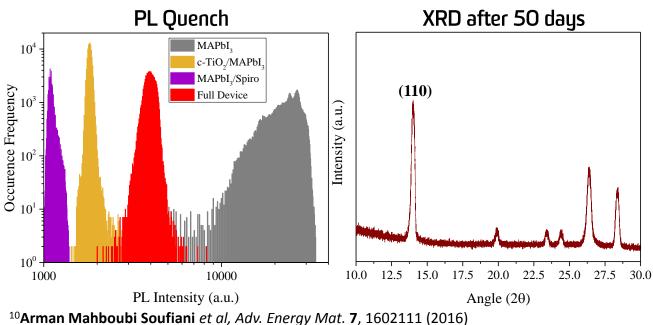
¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. **7**, 1602111 (2016)



Light-soaking at Open-circuit



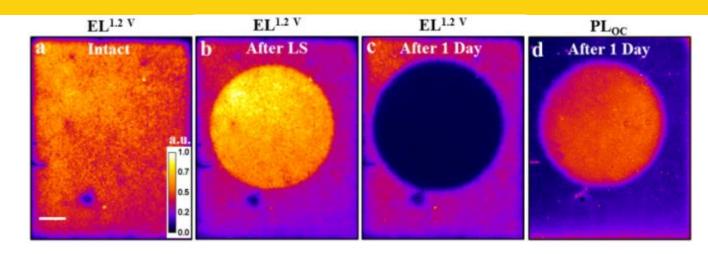


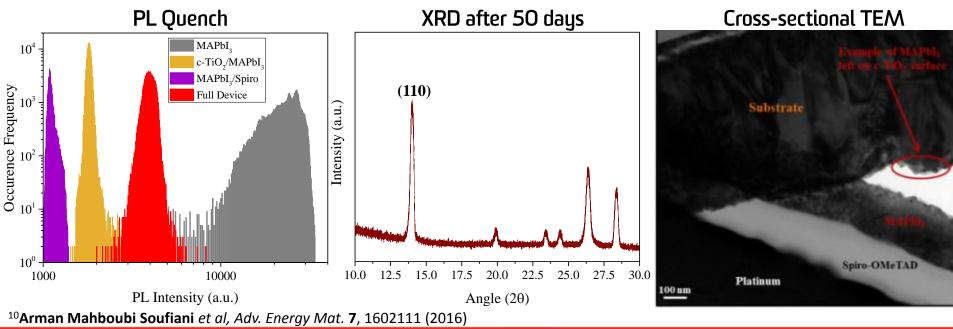




Light-soaking at Open-circuit



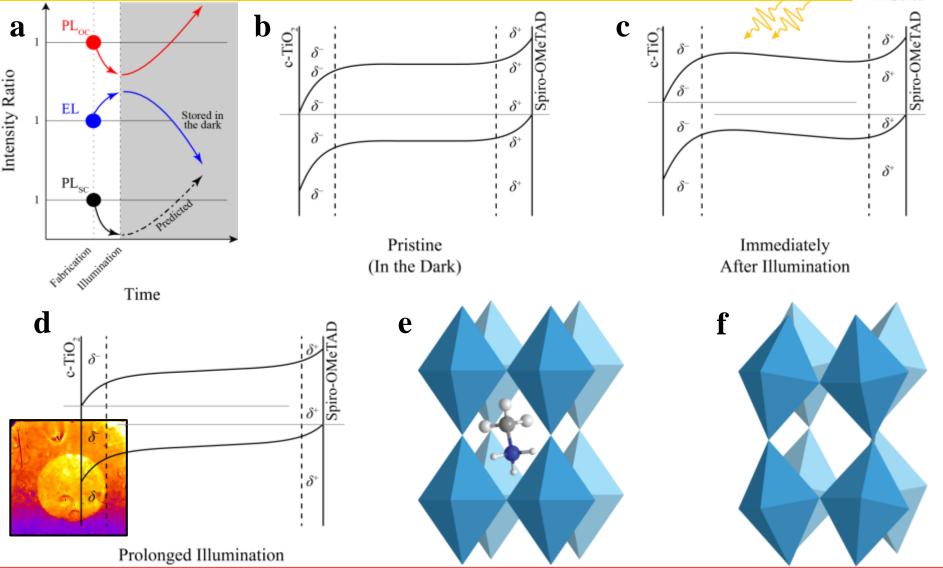






Proposed Mechanism



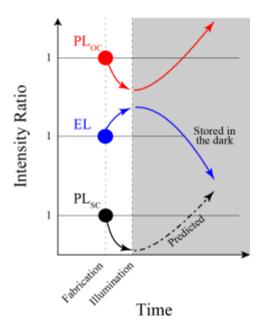




Conclusions



- Interfacial decoupling at TiO₂/CH₃NH₃PbI₃ was demonstrated for devices exposed to prolonged illumination.
- This has implications for credible solar cell degradation investigation.
- Experimental observations are explained based on ionic transport characteristics of organic-inorganic metal halide perovskites.¹⁰



¹⁰Arman Mahboubi Soufiani et al, Adv. Energy Mat. 7, 1602111 (2016)

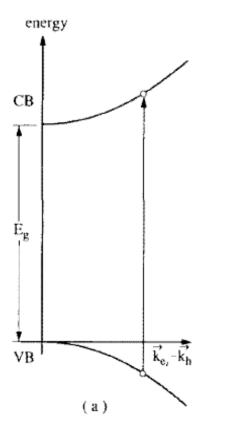


Introduction to Excitons in Polar Semiconductors



• Exciton:

- Effective mass approximation
- Hydrogen-like system



Electron Proton $Ry^* = \frac{m^*}{\varepsilon^2} \frac{13.6}{m_0}$ $E_n = E_g - Ry^* / n^2$

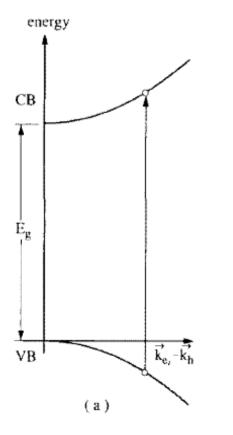
¹¹Klingshern, Semiconductor Optics (2012)

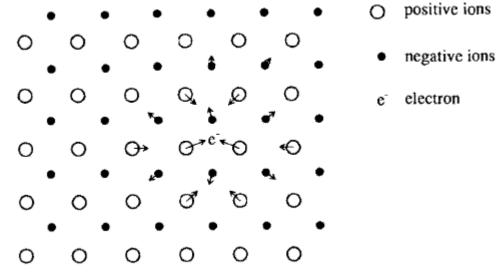




• Exciton:

- Effective mass approximation
- Hydrogen-like system





- Polaron:
 - Organic-inorganic lead halides have ionic bonds
 - Renormalizations due to polarons:
 - Increase in carrier effective mass,
 - Lowers the band gap,



¹¹Klingshern, Semiconductor Optics (2012)

Excitonic Properties (why is it important?)



The knowledge of excitonic binding energy is important:

- Determines the nature of the majority of photo-generated species,
- Device design optimization:
 - ✓ Large binding energies require an additional mechanism for exciton dissociation into free carriers through which they can readily contribute to the photocurrent,
- In OPV, large binding energy can result in extra loss in open-circuit voltage with respect to the bandgap,
- Influences PL response of the semiconductor,

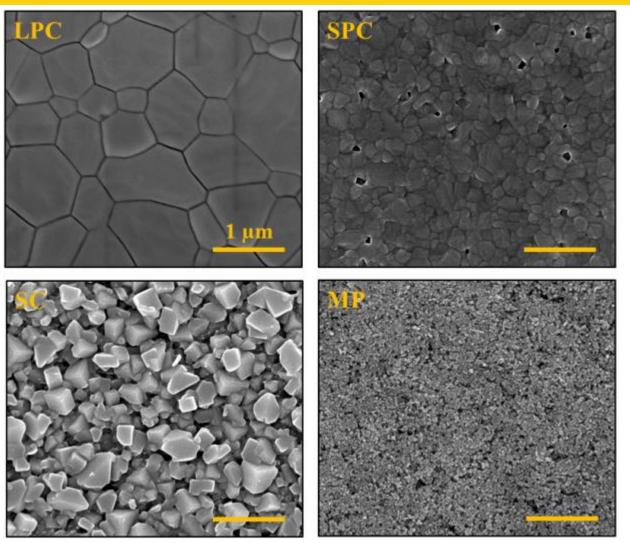
The knowledge of excitonic reduced mass is important:

• In determination of the charge-carrier mobility $\propto 1/m^{*}$



MAPbl₃ Morphologies





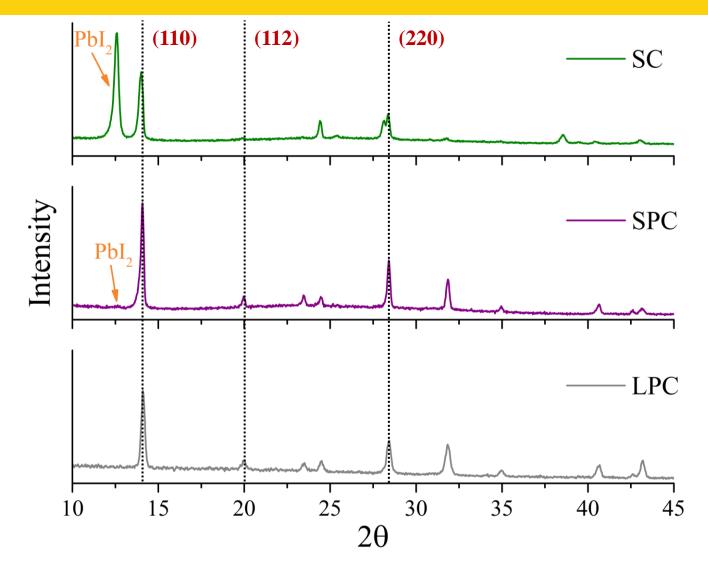
LPC: Large Polycrystalline SPC: Small Polycrystalline SC: Small Crystal MP: Mesoporous Al₂O₃

¹²Arman Mahboubi Soufiani et al, Energy Environ. Science **10**, 1358 (**2017**)



Structural Examination of MAPbl₃ (X-ray Diffraction)



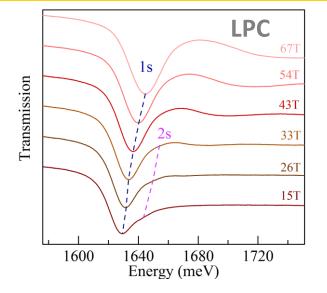


¹²Arman Mahboubi Soufiani et al, Energy Environ. Science **10**, 1358 (**2017**)



LPC MAPbl₃ Magneto-optic Response



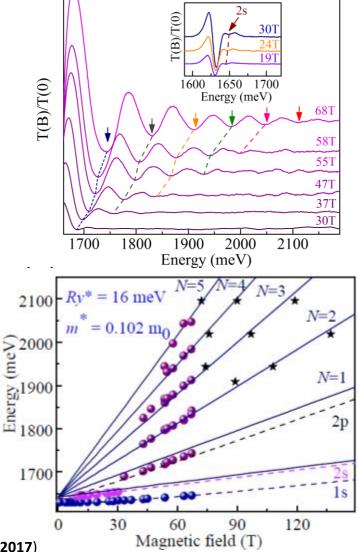


- Landau levels (i.e. free carrier states): Quantization of the free particle motion in the plane perpendicular to the magnetic field direction.
- Landau level transitions are described by:

$$E(B) = E_g + (N + 1/2)\hbar\omega_c$$

$$\hbar\omega_c = \hbar e B / m^*$$

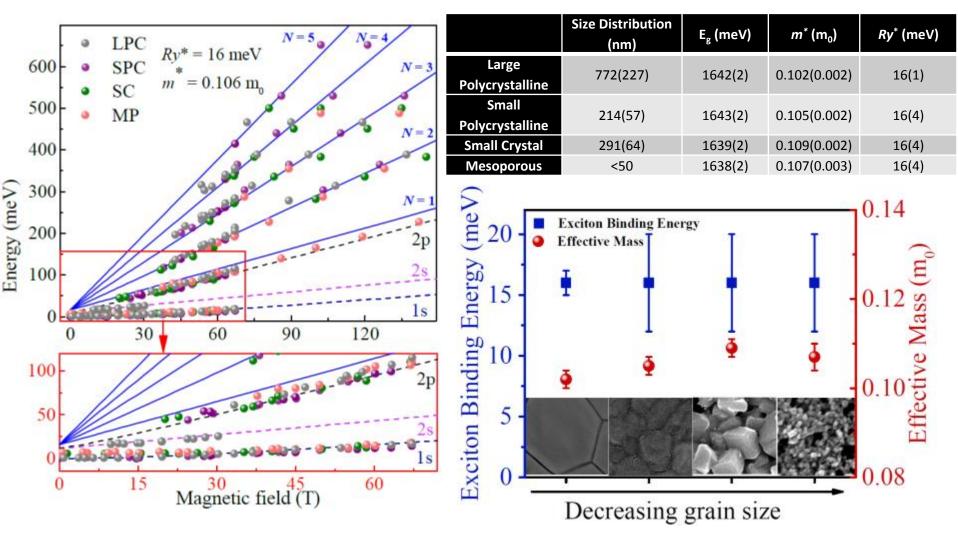
¹⁴Arman Mahboubi Soufiani et al, Energy Environ. Science **10**, 1358 (**2017**)





MAPbl₃ Magneto-optic Responses





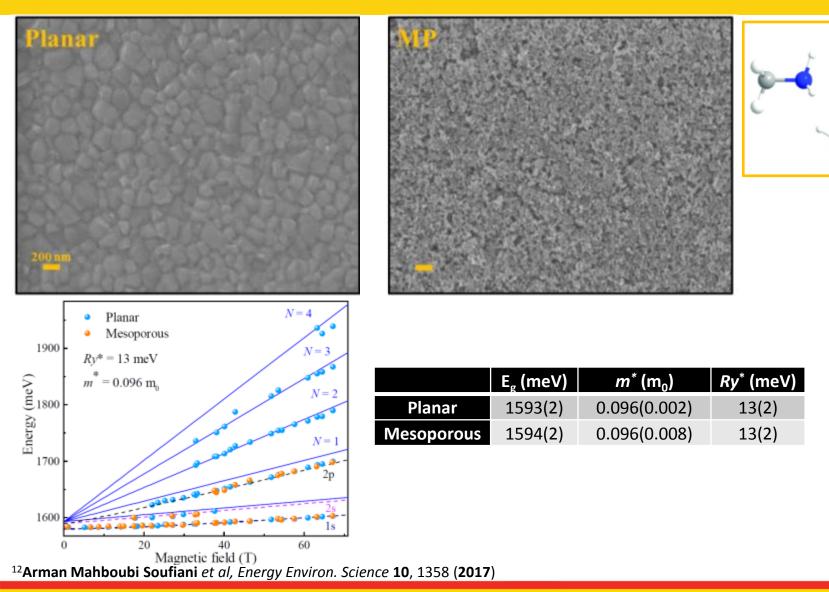
¹²Arman Mahboubi Soufiani et al, Energy Environ. Science 10, 1358 (2017)



Cs_{0.05}(MA_{0.17}FA_{0.83})_{0.95}Pb(I_{0.83}Br_{0.17})₃ Morphologies



Cs





Exciton-polaron Interaction



$$Ry^* = \frac{m^*}{\varepsilon^2} \frac{e^4}{2\hbar^2 (4\pi\varepsilon_0)^2};$$

$$a_{e,h} = \left(\frac{1}{\varepsilon_{\infty}} - \frac{1}{\varepsilon_{s}}\right) \frac{e^{2}}{2\hbar\omega_{LO}} \sqrt{\frac{2m_{e,h}\omega_{LO}}{\hbar}}$$

$$m_{e,h}^{p} \approx m_{e,h} (1 + \frac{a}{6} + \frac{a^{2}}{40} + ...) \qquad \frac{1}{m^{*}} = \frac{1}{m_{e}^{p}} + \frac{1}{m_{h}^{p}}$$



¹³Arman Mahboubi Soufiani, *PhD Thesis* (2017)



Conclusions



- Excitons truly play a negligible role in the operation of organic cation-based perovskites regardless of the thin film deposition technique and final morphology.
 - ✓ Universal values for CH₃NH₃Pbl₃ at 2 K:
 - *Ry*^{*}: **15-16 meV**
 - μ: 0.102-0.109m₀
 - ✓ Universal values for Cs_{0.05}(MA_{0.17}FA_{0.83})_{0.95}Pb(I_{0.83}Br_{0.17})₃ at 2 K:
 - Ry^* : **13**±2 meV
 - μ: 0.096±0.008m₀
- The electronic structure of the inorganic cage (e.g. PbI₃⁻ in CH₃NH₃PbI₃) is likely to have the greatest contribution to the excitonic properties of the perovskite semiconductors rather than the degree of poly-crystallinity and the order of dipolar organic-cation domains.
- Negligible influence of microstructure on the reduced mass implies that:
 - ✓ Polaron coupling constant (α) is only minimally influenced by the variation in microstructure.



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• My Family







Acknowledgements

ACAP

- My Family
- Prof. Richard Corkish
- Prof. Gavin Conibeer
- Prof. Martin Green
- Dr. Anita Ho-Baillie
- Dr. Murad Tayebjee
- Friends and colleagues









Khaju Bridge (Persian: پل خواجو Pol-e Khāju)

Thank You!

